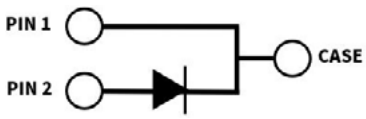
C4D10120E

1200 V, 10 A Silicon Carbide Schottky Diode

TO-252-2



Package Types: TO-252-2

PN: C4D10120

Features

- 1.2 kv Schottky rectifier
- Zero reverse recovery current
- High-frequency operation
- Temperature-independent switching behavior
- Extremely fast switching
- Positive temperature coefficient on V_F

Wolfspeed, Inc. is in the process of rebranding its products and related materials pursuant to the entity name change from Cree, Inc. to Wolfspeed, Inc. During this transition period, products received may be marked with either the Cree name and/or logo or the Wolfspeed name and/or logo.

Applications

- Solar inverters
- Switch mode power supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free wheeling diodes in inverter stages
- AC/DC converters

Benefits

- Replace bipolar with unipolar rectifiers
- Essentially no switching losses
- Higher efficiency
- Reduction of heat sink requirements
- Parallel devices without thermal runaway

Maximum Ratings (T_C = 25 °C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V		
Surge Peak Reverse Voltage	V_{RSM}	1300			
DC Blocking Voltage	V_{DC}	1200			
Continuous Forward Current	I_F	33	A	T_C = 25 °C	Fig. 3
		16		T_C = 135 °C	
		10		T_C = 156 °C	
Repetitive Peak Forward Surge Current	I_{FRM}	47		T_C = 25 °C, t_P = 10 ms, Half Sine Pulse	
		31.5		T_C = 110 °C, t_P = 10 ms, Half Sine Pulse	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	71		T_C = 25 °C, t_P = 10 ms, Half Sine Pulse	Fig. 8
		59		T_C = 110 °C, t_P = 10 ms, Half Sine Pulse	
Non-Repetitive Peak Forward Current	$I_{F, Max}$	750		T_C = 25 °C, t_P = 10 µs, Pulse	Fig. 8
		620		T_C = 110 °C, t_P = 10 µs, Pulse	
Power Dissipation	P_{tot}	166.5	W	T_C = 25 °C	Fig. 4
		72		T_C = 110 °C	
Diode dV/dt Ruggedness	dV/dt	200	V/ns	V_R = 0-960 V	
i²t Value	$\int i^2dt$	25	A^2s	T_C = 25 °C, t_P = 10 ms	
		17.5		T_C = 110 °C, t_P = 10 ms	
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to +175	°C		

Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Note
Forward Voltage	V_F	1.5	1.8	V	I_F = 10 A, T_J = 25 °C	Fig. 1
		2.2	3		I_F = 10 A, T_J = 175 °C	
Reverse Current	I_R	30	250	µA	V_R = 1200 V, T_J = 25 °C	Fig. 2
		55	350		V_R = 1200 V, T_J = 175 °C	
Total Capacitive Charge	Q_C	52		nC	V_R = 800 V, I_F = 10 A di/dt = 200 A/µS T_J = 25 °C	Fig. 5
Total Capacitance	C	754		pF	V_R = 0 V, T_J = 25 °C, f = 1 MHz	Fig. 6
		45			V_R = 400 V, T_J = 25 °C, f = 1 MHz	
		38			V_R = 800 V, T_J = 25 °C, f = 1 MHz	
Capacitance Stored Energy	E_C	14.5		µJ	V_R = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.9	°C/W	Fig. 9

Typical Performance

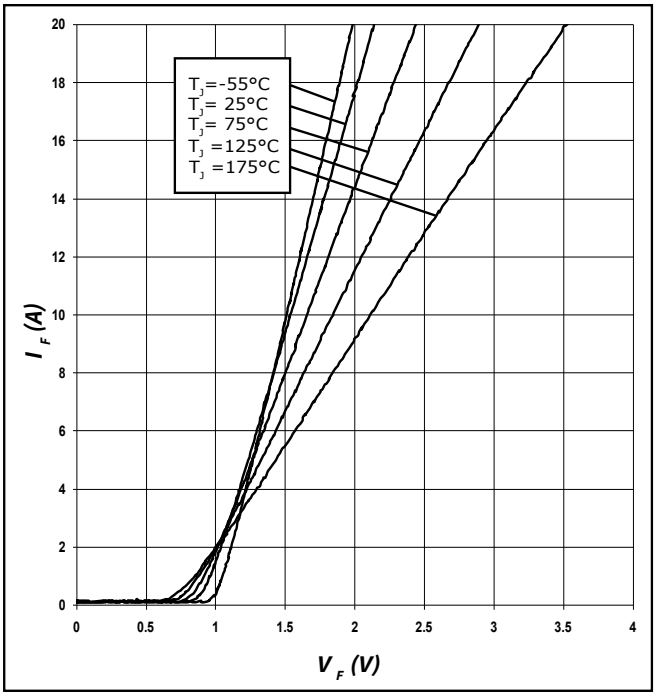


Figure 1. Forward Characteristics

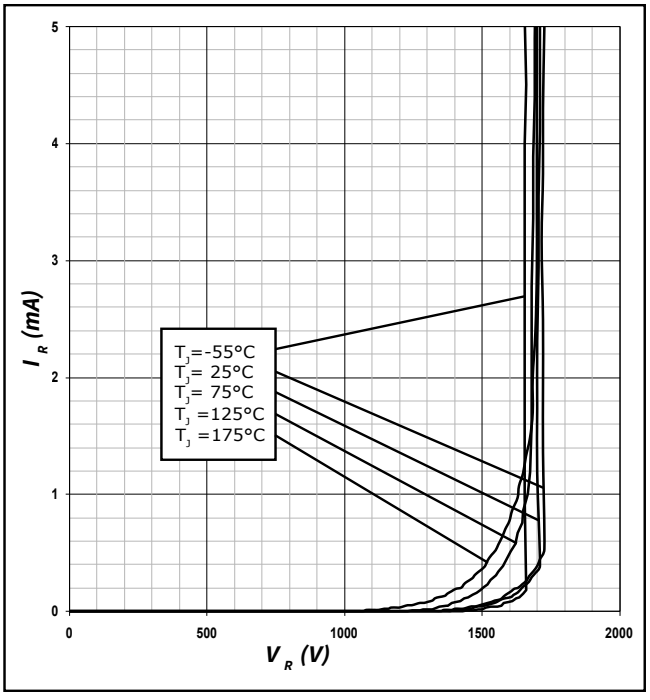


Figure 2. Reverse Characteristics

Typical Performance

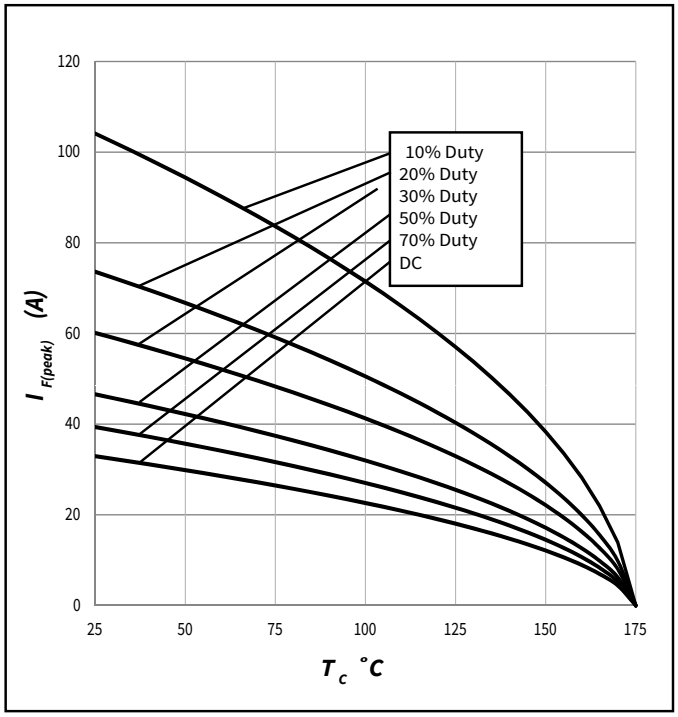


Figure 3. Current Derating

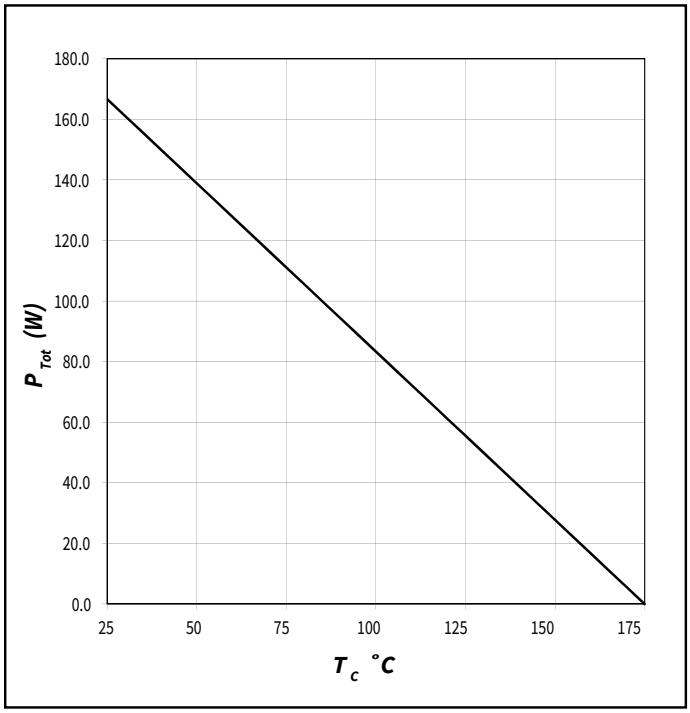


Figure 4. Power Derating

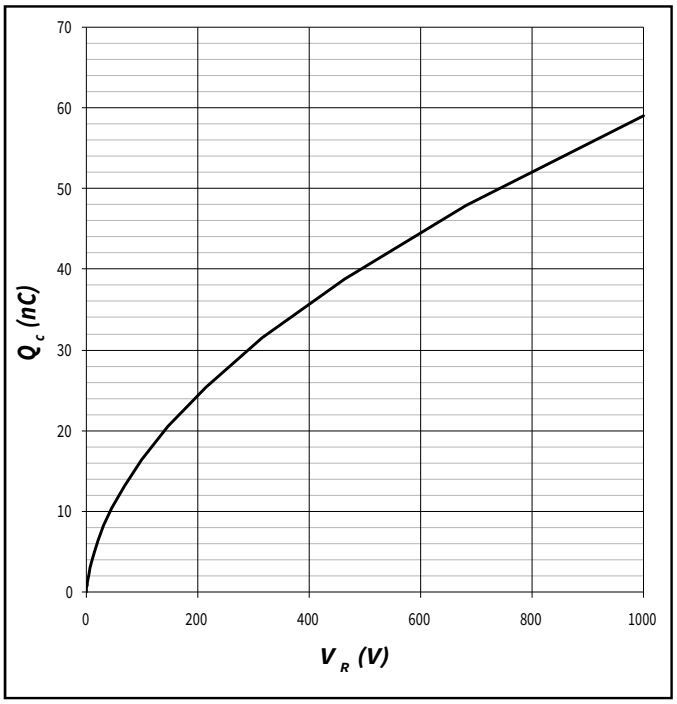


Figure 5. Recovery Charge vs. Reverse Voltage

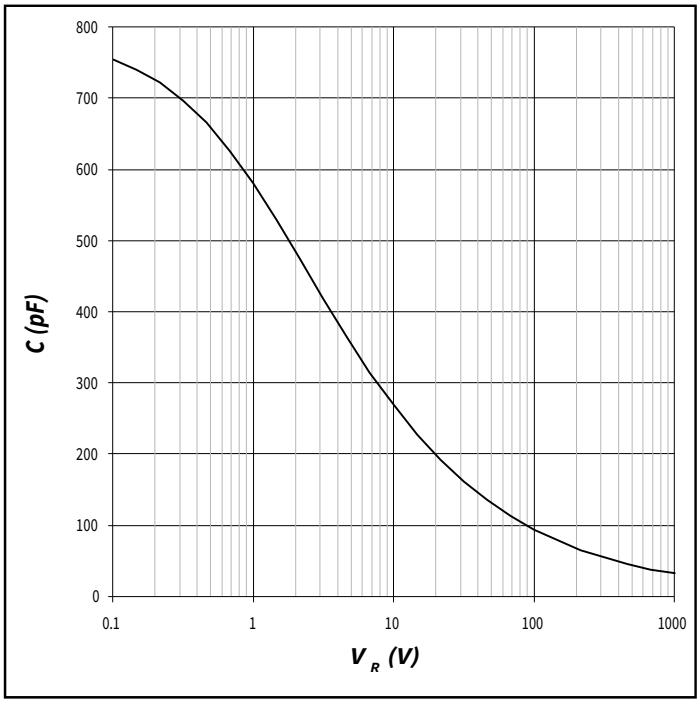


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

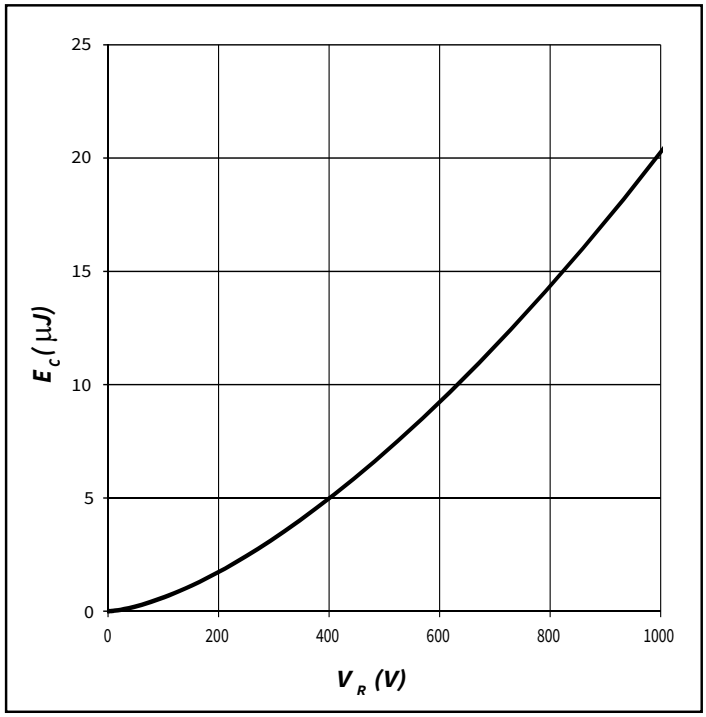


Figure 7. Typical Capacitance Stored Energy

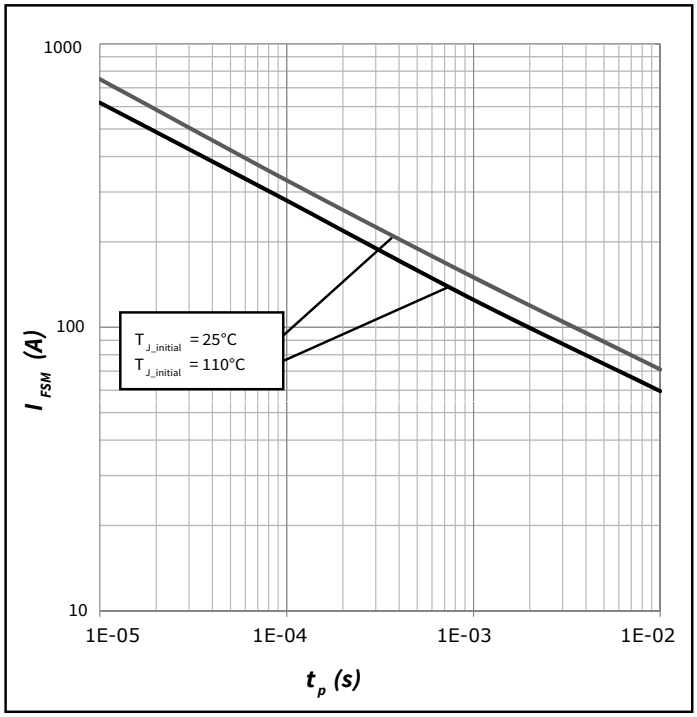


Figure 8. Non-Repetitive Peak Forward Surge Current Versus Pulse Duration (Sinusoidal Waveform)

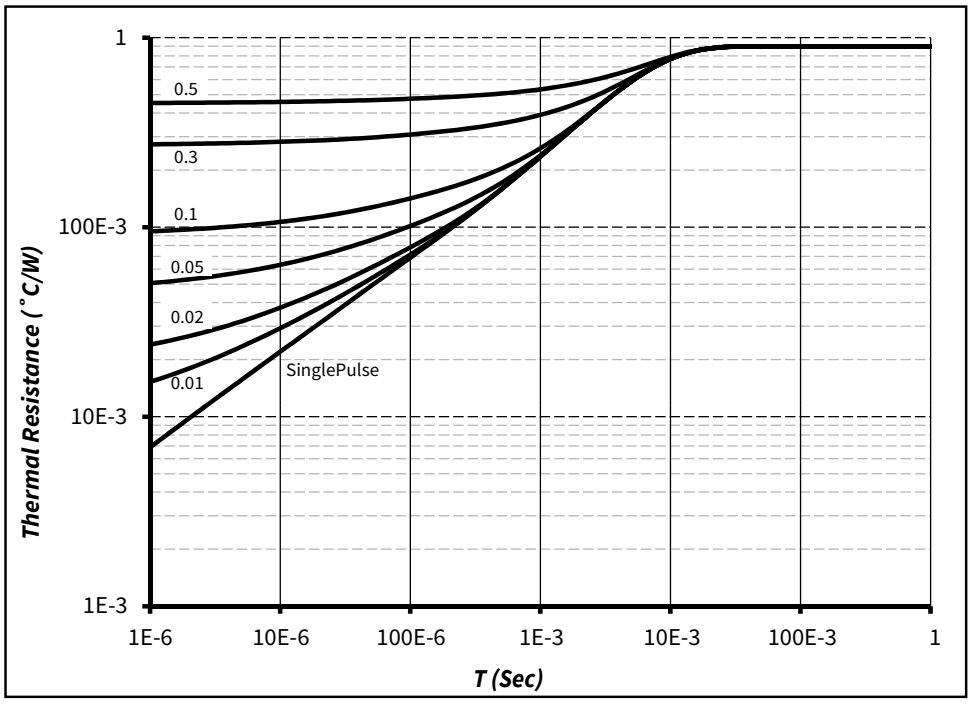
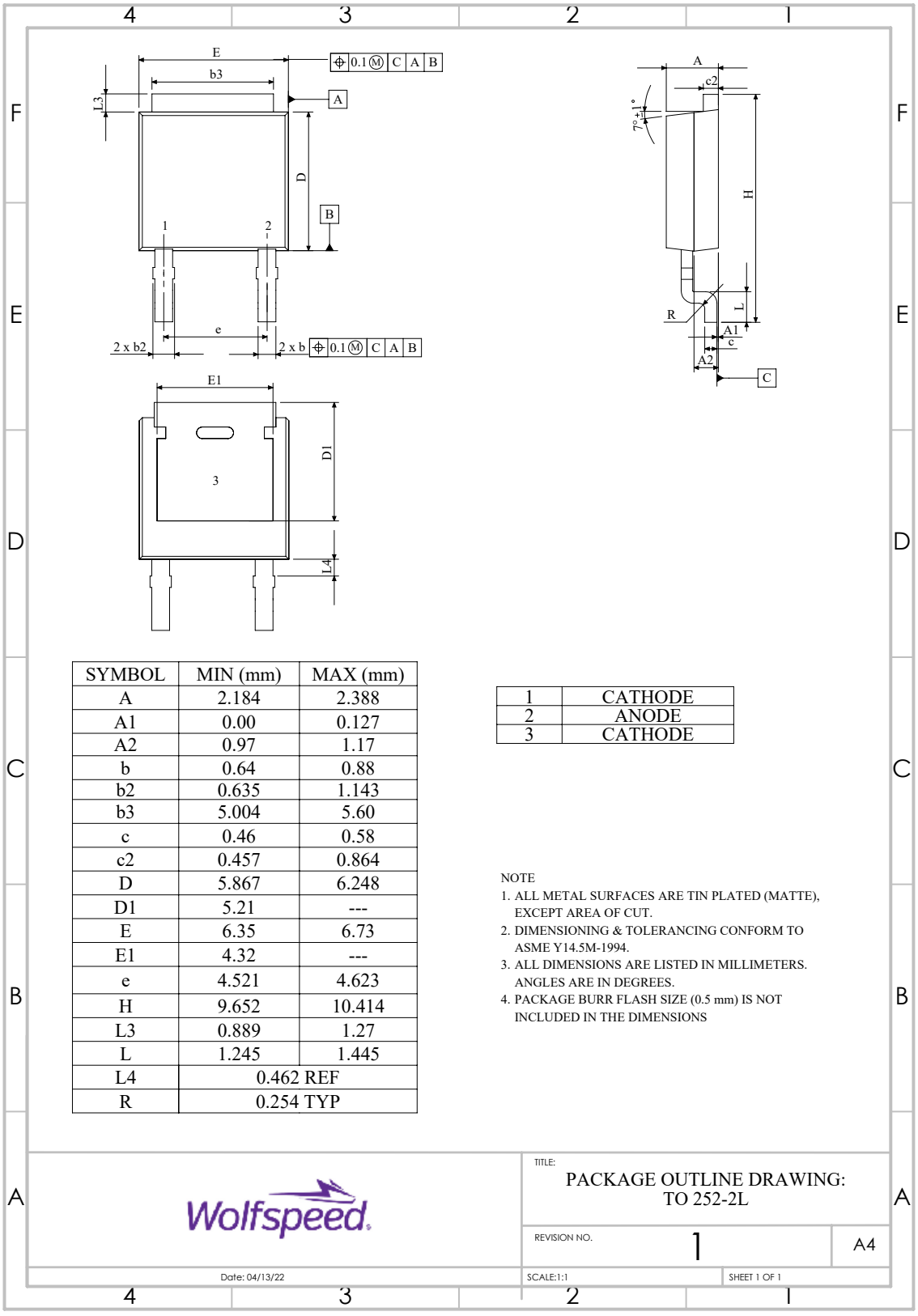


Figure 9. Transient Thermal Impedance

Package Dimensions

Package: TO-252-2



SYMBOL	MIN (mm)	MAX (mm)
A	2.184	2.388
A1	0.00	0.127
A2	0.97	1.17
b	0.64	0.88
b2	0.635	1.143
b3	5.004	5.60
c	0.46	0.58
c2	0.457	0.864
D	5.867	6.248
D1	5.21	---
E	6.35	6.73
E1	4.32	---
e	4.521	4.623
H	9.652	10.414
L3	0.889	1.27
L	1.245	1.445
L4	0.462 REF	
R	0.254 TYP	

1	CATHODE
2	ANODE
3	CATHODE

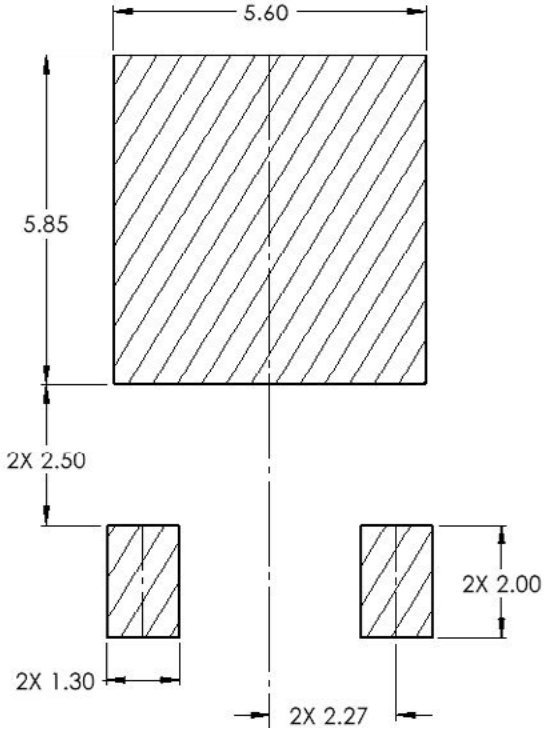
NOTE
1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
4. PACKAGE BURR FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

TITLE: PACKAGE OUTLINE DRAWING: TO 252-2L

REVISION NO. 1 | A4

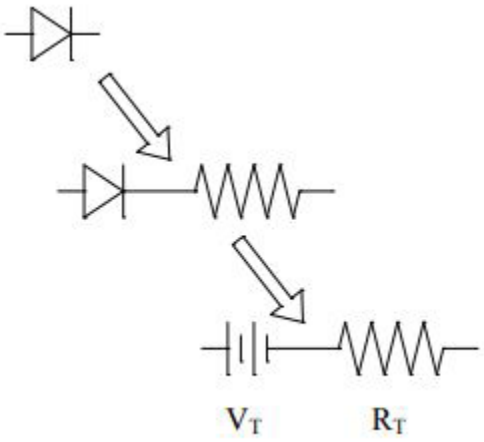
Date: 04/13/22 | SCALE:1:1 | SHEET 1 OF 1

Recommended Solder Pad Layout



Part Number	Package	Marking
C4D10120E	TO-252-2	C4D10120

Diode Model



$$V_{fT} = V_T + If * R_T$$

$$V_T = 0.98 + (T_J * -1.71 * 10^{-3})$$
$$R_T = 0.040 + (T_J * 5.32 * 10^{-4})$$

Note: T_J = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

Revision History

Current Revision	Date of Release	Description of Changes
9	September-2023	Updated Wolfspeed branding, package drawing, and solder pad layout
10	October-2023	Corrected solder pad layout and diode model

Notes & Disclaimer

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